

IGBT

英飞凌TRENCHSTOP™性能技术与 RAPID 1 快速反并联二极管共同封装

IKW30N60DTP

英飞凌600V DuoPack IGBT 和二极管

TRENCHSTOP™高性能系列

数据手册

采用 Trench 和 Fieldstop 技术的高速 IGBT

特性：

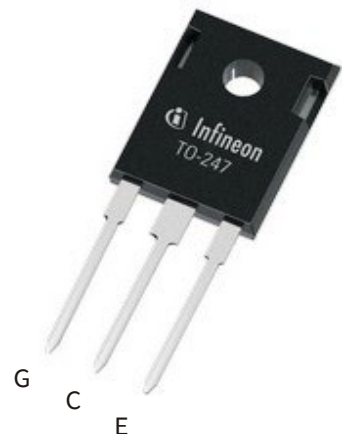
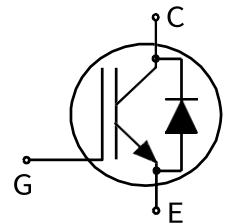
TRENCHSTOP™ 技术产品

- 极低 V_{CEsat}
- 低关断损耗
- 低拖尾电流
- 低电磁干扰
- 非常柔软、快速恢复的反并联二极管
- 最高结温 175°C
- 符合 JEDEC 目标应用要求
- 无铅镀层；符合 RoHS 标准
- 完整的产品品类和 PSpice 模型：

<http://www.infineon.com/igbt/>

应用：

- 驱动器
- 太阳能逆变器
- UPS（不间断电源）
- 中等开关频率转换器



关键性能和封装参数

Type	V_{CE}	I_C	$V_{CEsat}, T_{vj}=25^{\circ}C$	T_{vjmax}	Marking	Package
IKW30N60DTP	600V	30A	1.6V	175°C	K30DDTP	PG-TO247-3

本数据手册的原文使用英文撰写。为方便起见，英飞凌提供了译文；由于翻译过程中可能使用了自动化工具，英飞凌不保证译文的准确性。为确认准确性，请务必访问 [infineon.com](http://www.infineon.com) 参考最新的英文版本（控制文档）。

目录

描述.....	2
目录.....	3
最大额定值.....	4
热阻抗.....	4
电气特性.....	5
电气特性图	7
封装图.....	14
测试状况.....	15
修订记录.....	16
免责声明.....	16

最大额定值

注意：为了获得最佳的使用寿命和可靠性，英飞凌建议运行条件不超过本数据手册中所述最大额定值的 80%。

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_{vj} \geq 25^{\circ}\text{C}$	V_{CE}	600	V
DC collector current, limited by T_{vjmax} $T_C = 25^{\circ}\text{C}$ $T_C = 100^{\circ}\text{C}$	I_C	53.0 38.0	A
Pulsed collector current, t_p limited by T_{vjmax} ¹⁾	I_{Cpuls}	90.0	A
Turn off safe operating area $V_{CE} \leq 600\text{V}$, $T_{vj} \leq 175^{\circ}\text{C}$, $t_p = 1\mu\text{s}$ ¹⁾	-	90.0	A
Diode forward current, limited by T_{vjmax} $T_C = 25^{\circ}\text{C}$ $T_C = 100^{\circ}\text{C}$	I_F	39.0 24.0	A
Diode pulsed current, t_p limited by T_{vjmax} ¹⁾	I_{Fpuls}	90.0	A
Gate-emitter voltage	V_{GE}	± 20	V
Short circuit withstand time $V_{GE} = 15.0\text{V}$, $V_{CC} \leq 400\text{V}$ Allowed number of short circuits < 1000 Time between short circuits: $\geq 1.0\text{s}$ $T_{vj} = 150^{\circ}\text{C}$	t_{SC}	5	μs
Power dissipation $T_C = 25^{\circ}\text{C}$ Power dissipation $T_C = 100^{\circ}\text{C}$	P_{tot}	200.0 100.0	W
Operating junction temperature	T_{vj}	$-40...+175$	$^{\circ}\text{C}$
Storage temperature	T_{stg}	$-55...+150$	$^{\circ}\text{C}$
Soldering temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	$^{\circ}\text{C}$
Mounting torque, M3 screw Maximum of mounting processes: 3	M	0.6	Nm

热阻抗

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
R _{th} Characteristics						
IGBT thermal resistance, junction - case	R _{th(j-c)}		-	0.50	0.75	K/W
Diode thermal resistance, junction - case	R _{th(j-c)}		-	0.99	1.55	K/W

¹⁾由设计标定，不受限于生产测试。

电气特性，测于 $T_{vj} = 25^{\circ}\text{C}$ 的条件下，除非另有规定

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0V, I_C = 2.00mA$	600	-	-	V
Collector-emitter saturation voltage	V_{CEsat}	$V_{GE} = 15.0V, I_C = 30.0A$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 175^{\circ}C$	- -	1.60 1.94	1.80 -	V
Diode forward voltage	V_F	$V_{GE} = 0V, I_F = 15.0A$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 175^{\circ}C$	- -	1.45 1.39	1.70 -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C = 0.48mA, V_{CE} = V_{GE}$	4.1	5.1	5.7	V
Zero gate voltage collector current	I_{CES}	$V_{CE} = 600V, V_{GE} = 0V$ $T_{vj} = 25^{\circ}C$ $T_{vj} = 175^{\circ}C$	- -	- -	40 -	μA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0V, V_{GE} = 20V$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE} = 20V, I_C = 30.0A$	-	26.0	-	S

电气特性，测于 $T_{vj} = 25^{\circ}\text{C}$ 的条件下，除非另有规定

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Dynamic Characteristic						
Input capacitance	C_{ies}	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$	-	1050	-	pF
Output capacitance	C_{oes}		-	58	-	
Reverse transfer capacitance	C_{res}		-	36	-	
Gate charge	Q_G	$V_{CC} = 480V, I_C = 30.0A,$ $V_{GE} = 15V$	-	130.0	-	nC
Internal emitter inductance measured 5mm (0.197 in.) from case	L_E		-	13.0	-	nH
Short circuit collector current Max. 1000 short circuits Time between short circuits: $\geq 1.0s$	$I_{C(SC)}$	$V_{GE} = 15.0V, V_{CC} \leq 400V,$ $t_{SC} \leq 5\mu s$ $T_{vj} = 150^{\circ}C$	-	137	-	A

开关特性、感性负载

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic, at $T_{vj} = 25^{\circ}\text{C}$						
Turn-on delay time	$t_{d(\text{on})}$	$T_{vj} = 25^{\circ}\text{C},$ $V_{CC} = 400\text{V}, I_C = 30.0\text{A},$ $V_{GE} = 0.0/15.0\text{V},$ $R_{G(\text{on})} = 10.5\Omega, R_{G(\text{off})} = 10.5\Omega,$ $L_{\sigma} = 32\text{nH}, C_{\sigma} = 60\text{pF}$ L_{σ}, C_{σ} from Fig. E Energy losses include “tail” and diode reverse recovery.	-	15	-	ns
Rise time	t_r		-	21	-	ns
Turn-off delay time	$t_{d(\text{off})}$		-	179	-	ns
Fall time	t_f		-	12	-	ns
Turn-on energy	E_{on}		-	0.71	-	mJ
Turn-off energy	E_{off}		-	0.42	-	mJ
Total switching energy	E_{ts}		-	1.13	-	mJ

Diode reverse recovery time	t_{rr}	$T_{vj} = 25^{\circ}\text{C},$ $V_R = 400\text{V}, I_F$ $= 15.0\text{A},$ $di_F/dt = 1160\text{A}/\mu\text{s}$	-	76	-	ns
Diode reverse recovery charge	Q_{rr}		-	0.45	-	μC
Diode peak reverse recovery current	I_{rrm}		-	10.2	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	150	-	A/ μs

开关特性、感性负载

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	

IGBT Characteristic, at $T_{vj} = 175^{\circ}\text{C}$

Turn-on delay time	$t_{d(on)}$	$T_{vj} = 175^{\circ}\text{C},$ $V_{CC} = 400\text{V}, I_C = 30.0\text{A},$ $V_{GE} = 0.0/15.0\text{V},$ $R_{G(on)} = 10.5\Omega, R_{G(off)} = 10.5\Omega,$ $L\sigma = 32\text{nH}, C\sigma = 60\text{pF}$ $L\sigma, C\sigma$ from Fig. E Energy losses include "tail" and diode reverse recovery.	-	15	-	ns
Rise time	t_r		-	23	-	ns
Turn-off delay time	$t_{d(off)}$		-	220	-	ns
Fall time	t_f		-	59	-	ns
Turn-on energy	E_{on}		-	0.99	-	mJ
Turn-off energy	E_{off}		-	0.74	-	mJ
Total switching energy	E_{ts}		-	1.73	-	mJ

Diode reverse recovery time	t_{rr}	$T_{vj} = 175^{\circ}\text{C}, V_R$ $= 400\text{V}, I_F =$ $15.0\text{A},$ $di_F/dt = 1160\text{A}/\mu\text{s}$	-	134	-	ns
Diode reverse recovery charge	Q_{rr}		-	1.23	-	μC
Diode peak reverse recovery current	I_{rrm}		-	16.6	-	A
Diode peak rate of fall of reverse recovery current during t_b	di_{rr}/dt		-	135	-	A/ μs

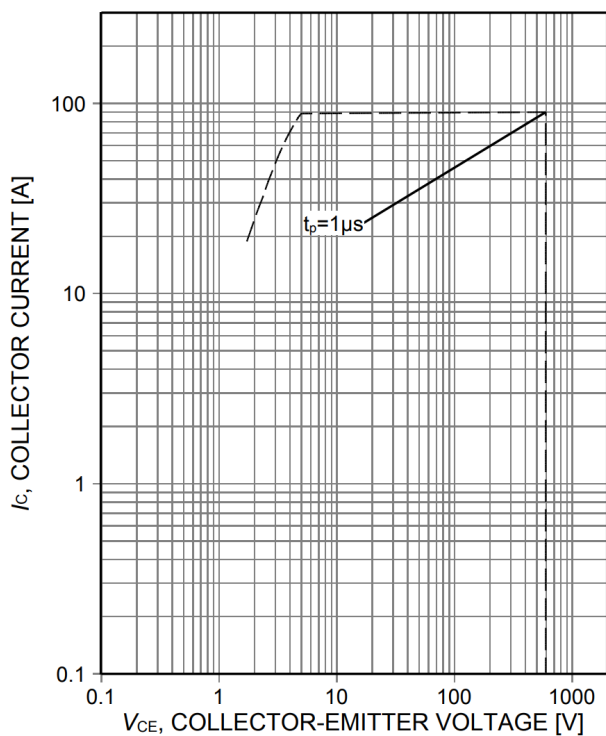


Figure 1. **Forward bias safe operating area**
($D=0$, $T_C=25^\circ\text{C}$, $T_J\leq 175^\circ\text{C}$; $V_{GE}=15\text{V}$)

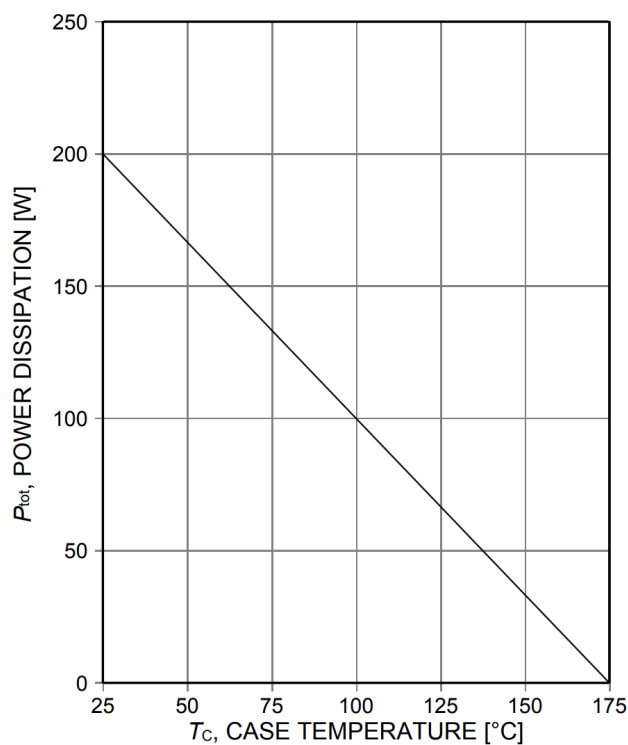


Figure 2. **Power dissipation as a function of case temperature**
($T_J\leq 175^\circ\text{C}$)

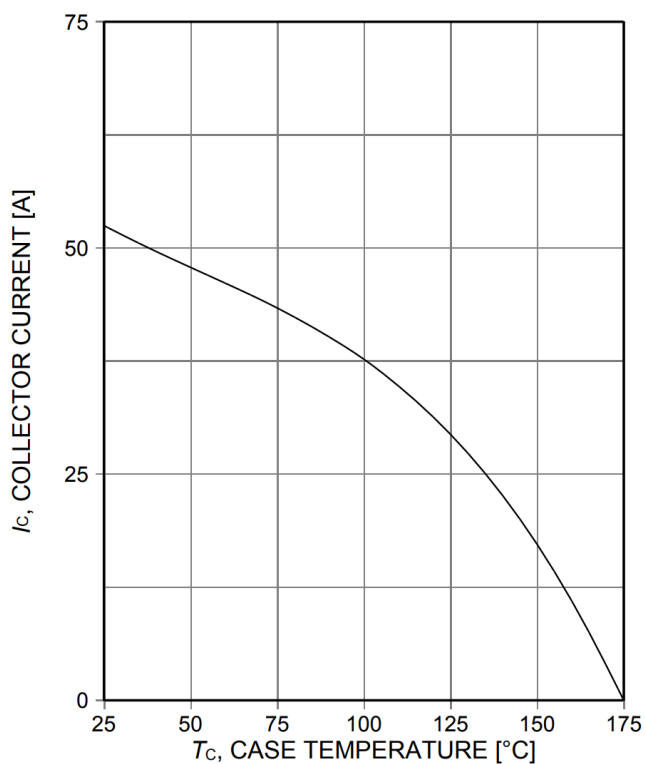


Figure 3. **Collector current as a function of case temperature**
($V_{GE}\geq 15\text{V}$, $T_J\leq 175^\circ\text{C}$)

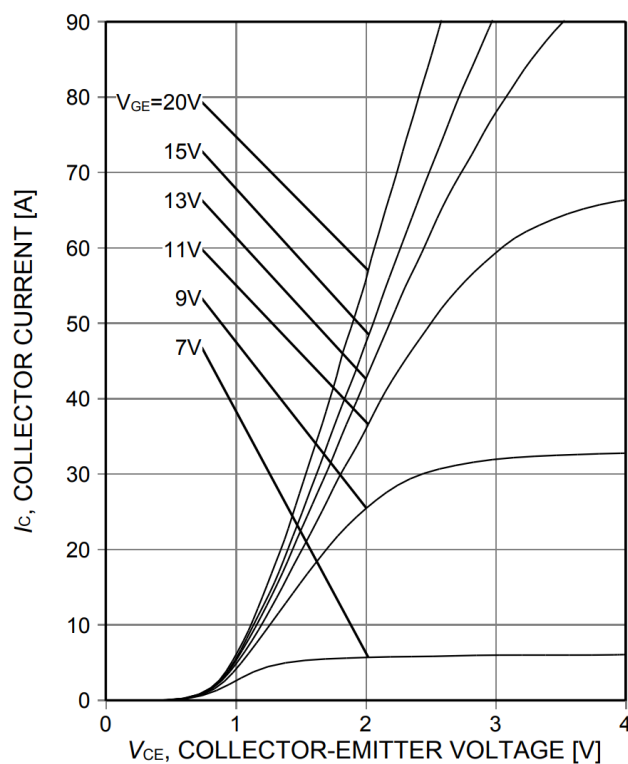


Figure 4. **Typical output characteristic**
($T_J=25^\circ\text{C}$)

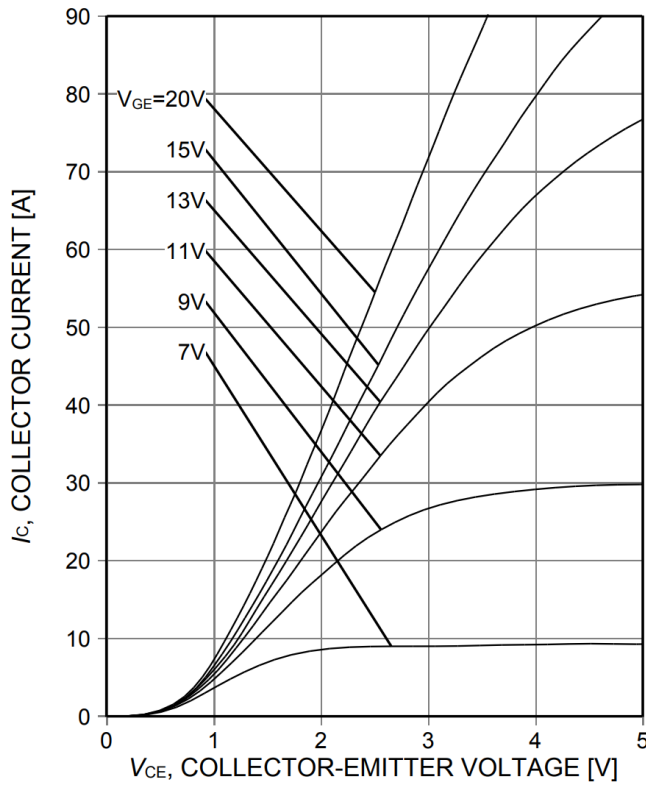


Figure 5. **Typical output characteristic**
($T_j=175^\circ\text{C}$)

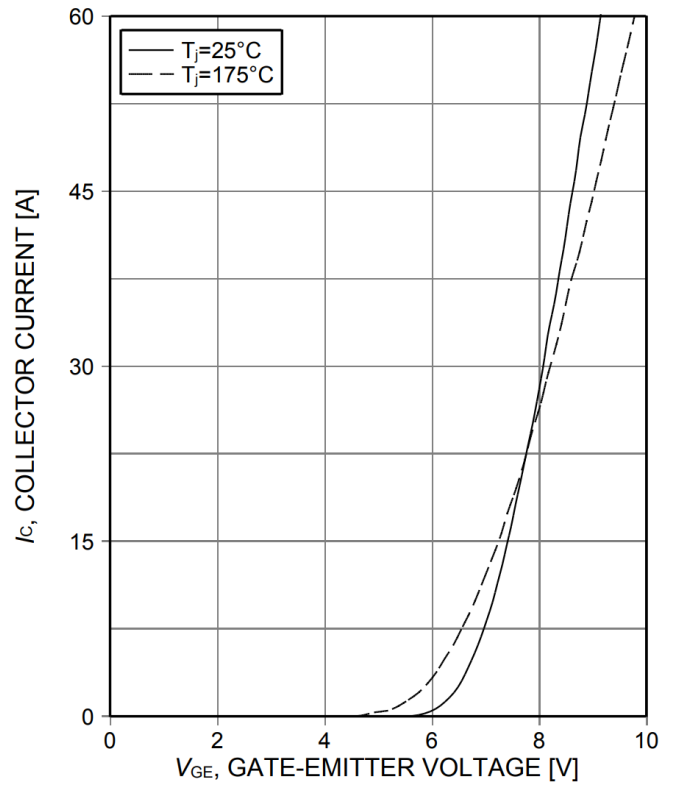


Figure 6. **Typical transfer characteristic**
($V_{CE}=20\text{V}$)

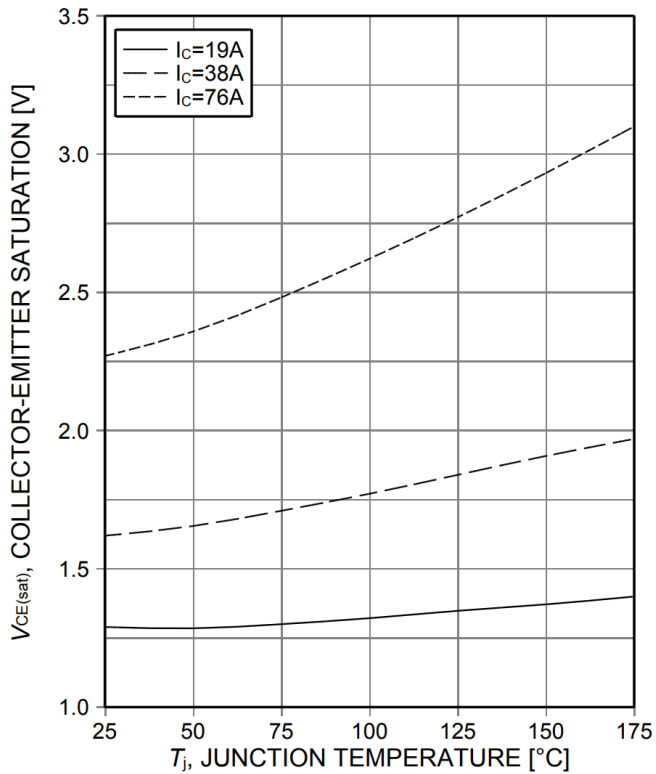


Figure 7. **Typical collector-emitter saturation voltage as a function of junction temperature**
($V_{GE}=15\text{V}$)

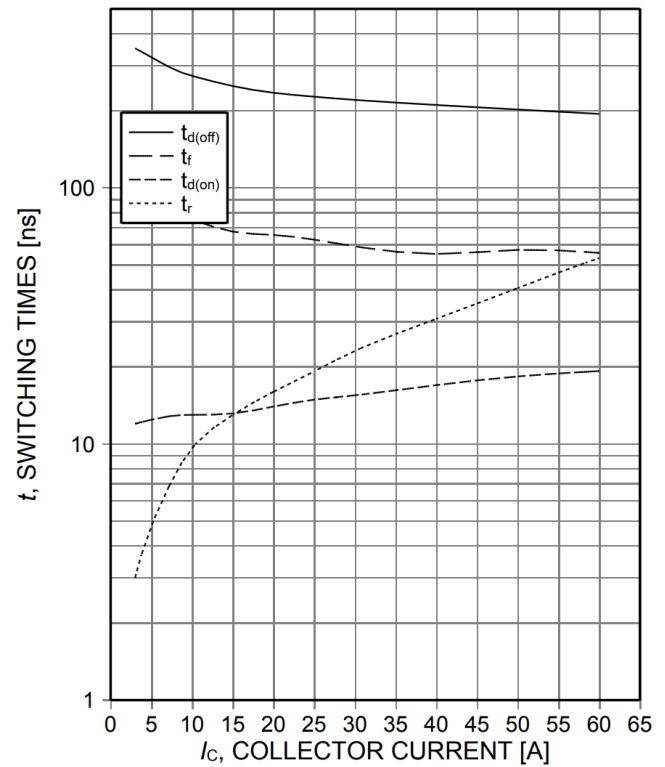


Figure 8. **Typical switching times as a function of collector current**
(ind. load, $T_j=175^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $r_G=10.5\Omega$, test circuit in Fig. E)

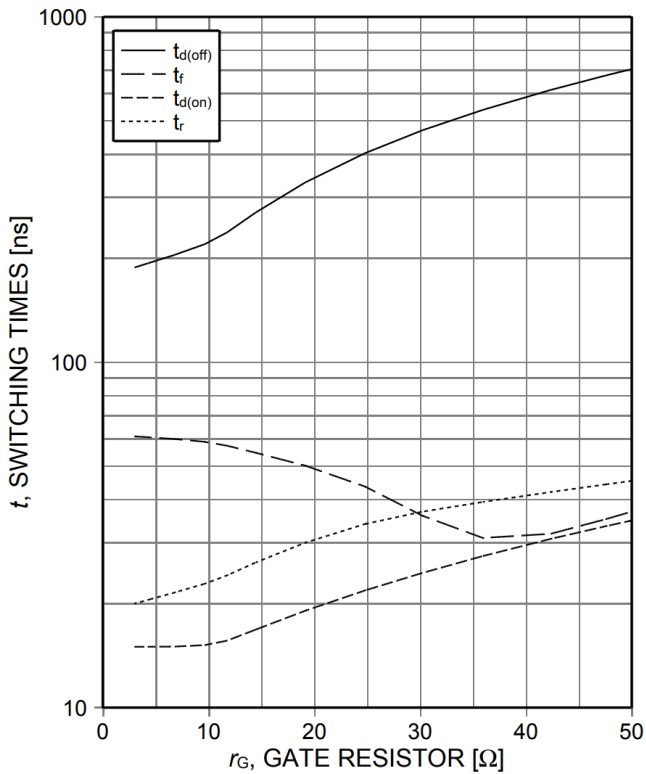


Figure 9. **Typical switching times as a function of gate resistor**
(ind. load, $T_j=175^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=30\text{A}$, test circuit in Fig. E)

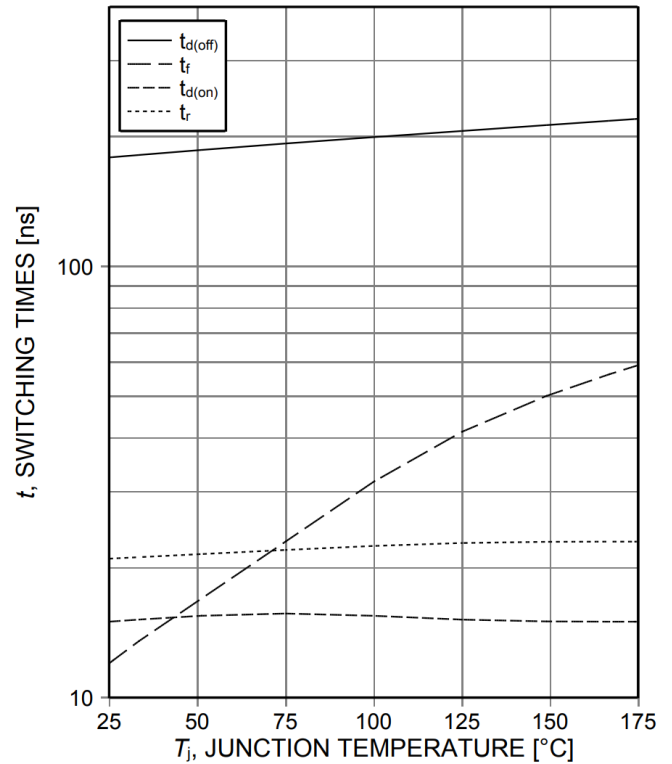


Figure 10. **Typical switching times as a function of junction temperature**
(ind. load, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=30\text{A}$, $r_G=10.5\Omega$, test circuit in Fig. E)

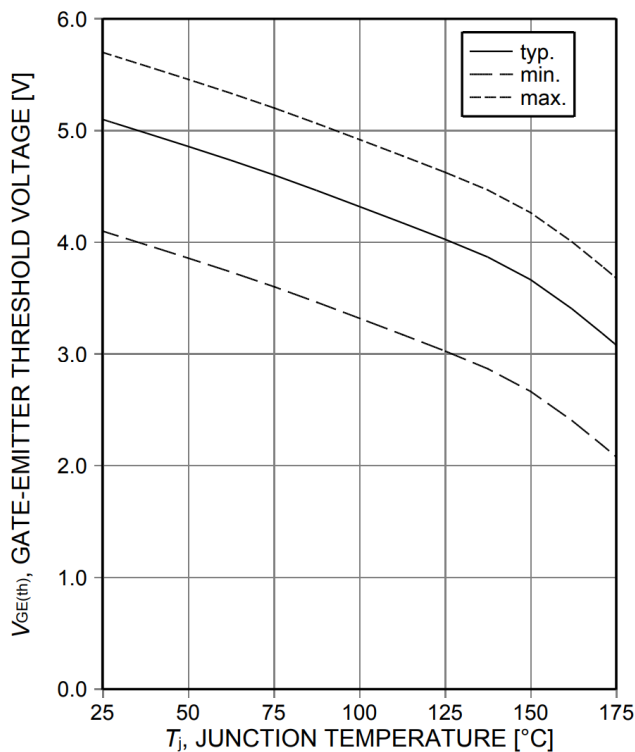


Figure 11. **Gate-emitter threshold voltage as a function of junction temperature**
($I_C=0.48\text{mA}$)

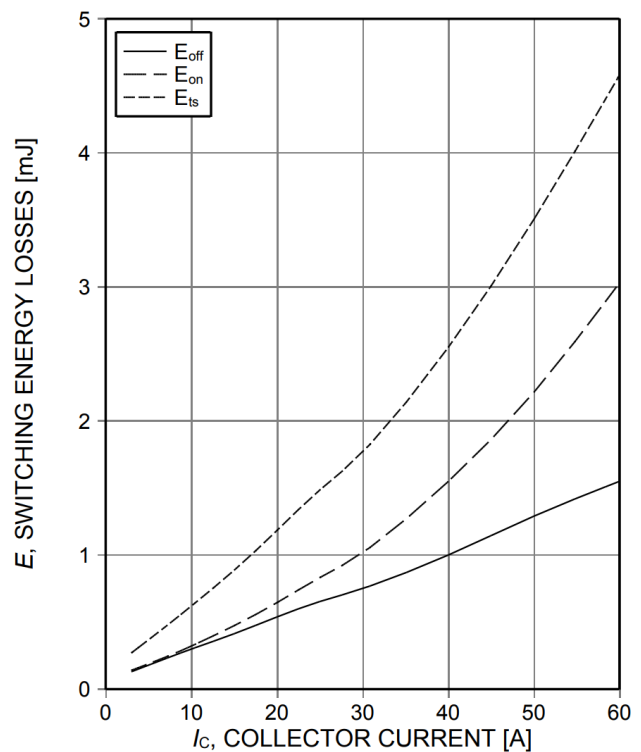


Figure 12. **Typical switching energy losses as a function of collector current**
(ind. load, $T_j=175^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $r_G=10.5\Omega$, test circuit in Fig. E)

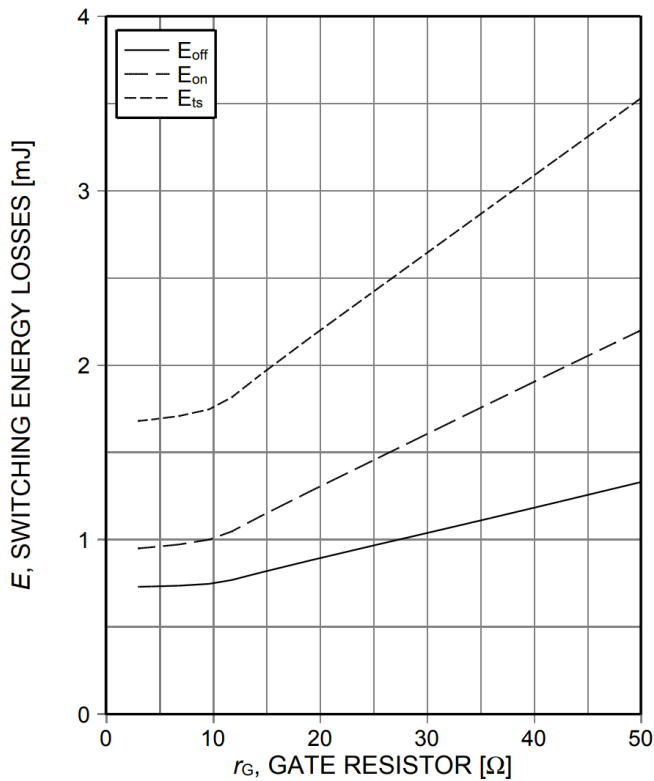


Figure 13. **Typical switching energy losses as a function of gate resistor**
(ind. load, $T_j=175^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=30\text{A}$, test circuit in Fig. E)

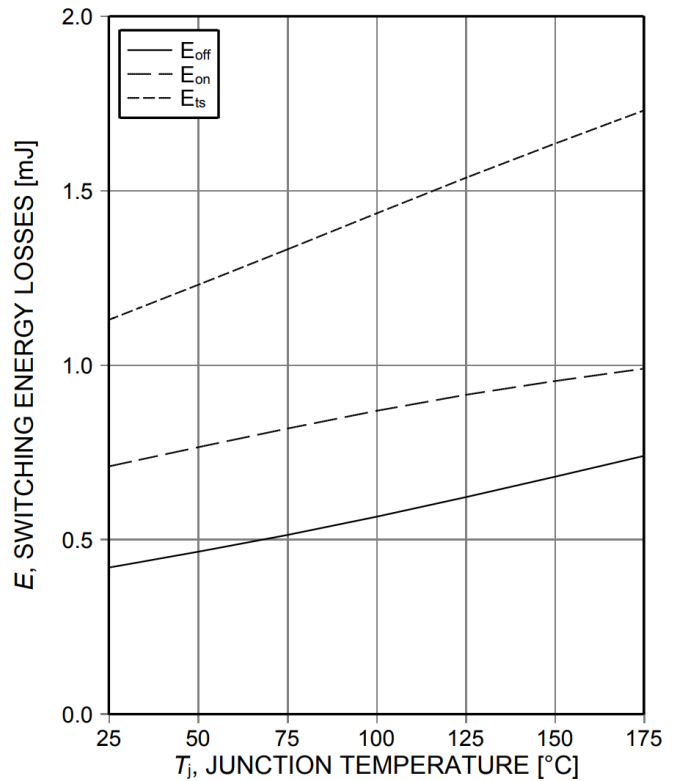


Figure 14. **Typical switching energy losses as a function of junction temperature**
(ind. load, $V_{CE}=400\text{V}$, $V_{GE}=15/0\text{V}$, $I_C=30\text{A}$, $r_G=10.5\Omega$, test circuit in Fig. E)

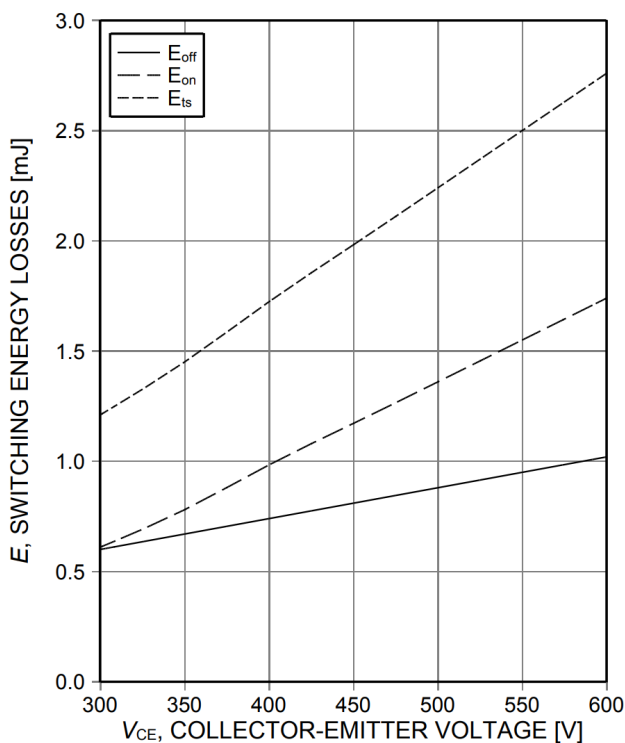


Figure 15. **Typical switching energy losses as a function of collector emitter voltage**
(ind. load, $T_j=175^\circ\text{C}$, $V_{GE}=15/0\text{V}$, $I_C=30\text{A}$, $r_G=10.5\Omega$, test circuit in Fig. E)

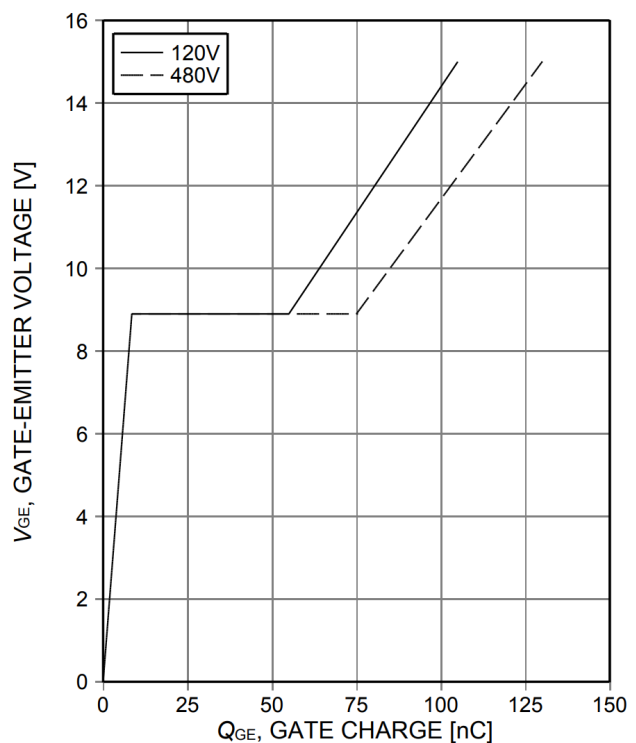


Figure 16. **Typical gate charge**
($I_C=30\text{A}$)

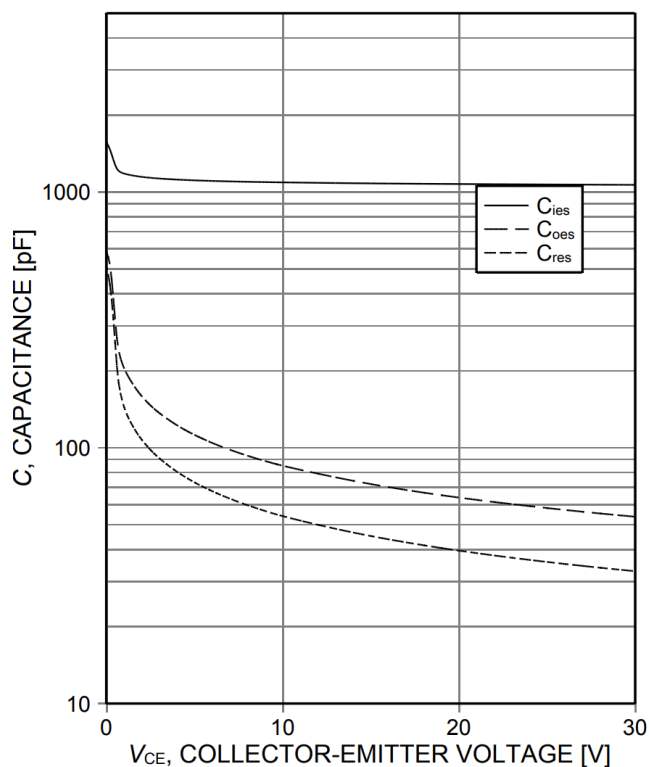


Figure 17. **Typical capacitance as a function of collector-emitter voltage**
($V_{GE}=0V$, $f=1MHz$)

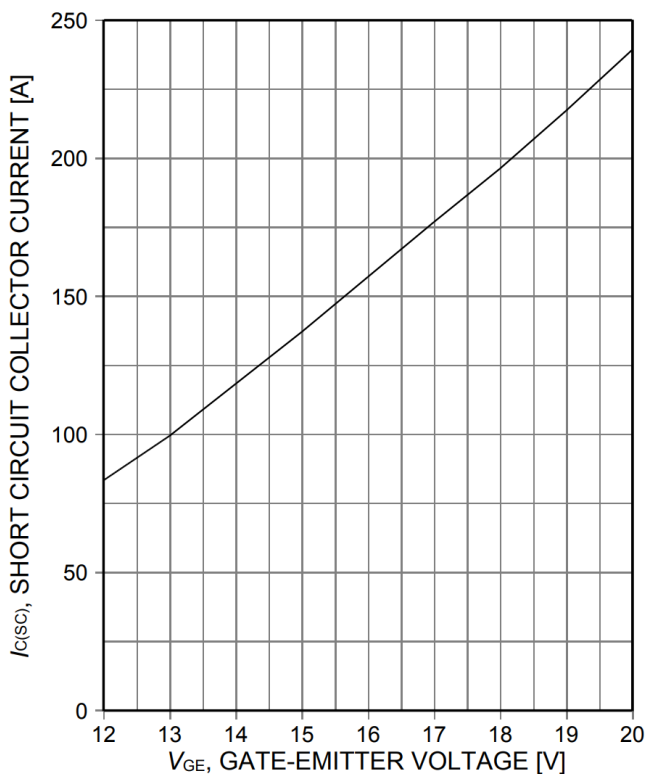


Figure 18. **Typical short circuit collector current as a function of gate-emitter voltage**
($V_{CE} \leq 400V$, start at $T_J=25^\circ C$)

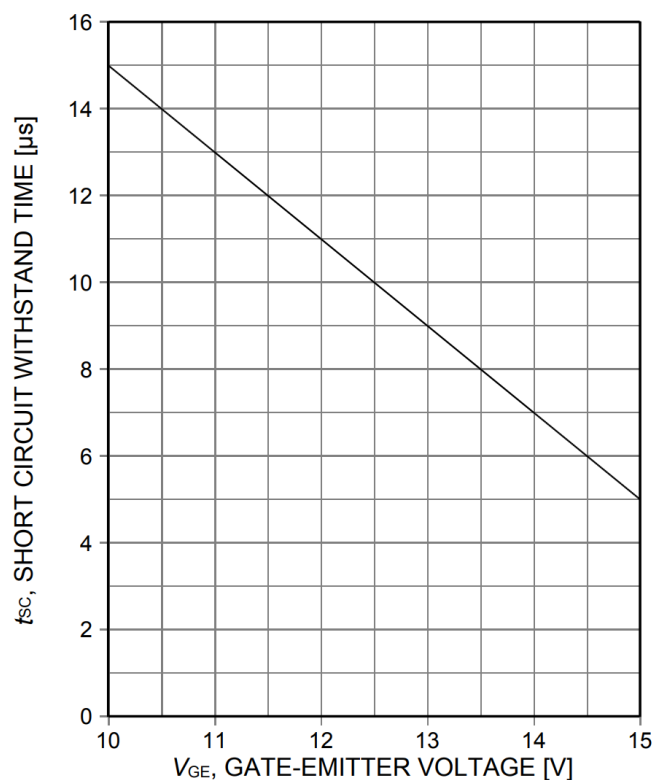


Figure 19. **Short circuit withstand time as a function of gate-emitter voltage**
($V_{CE} \leq 400V$, start at $T_J \leq 150^\circ C$)

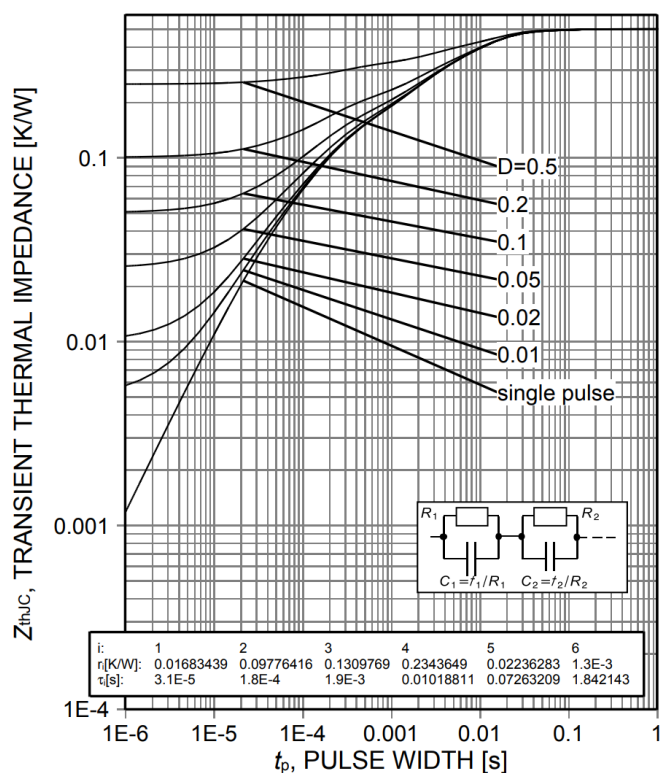


Figure 20. **Typical IGBT transient thermal impedance**
($D=t_p/T$)

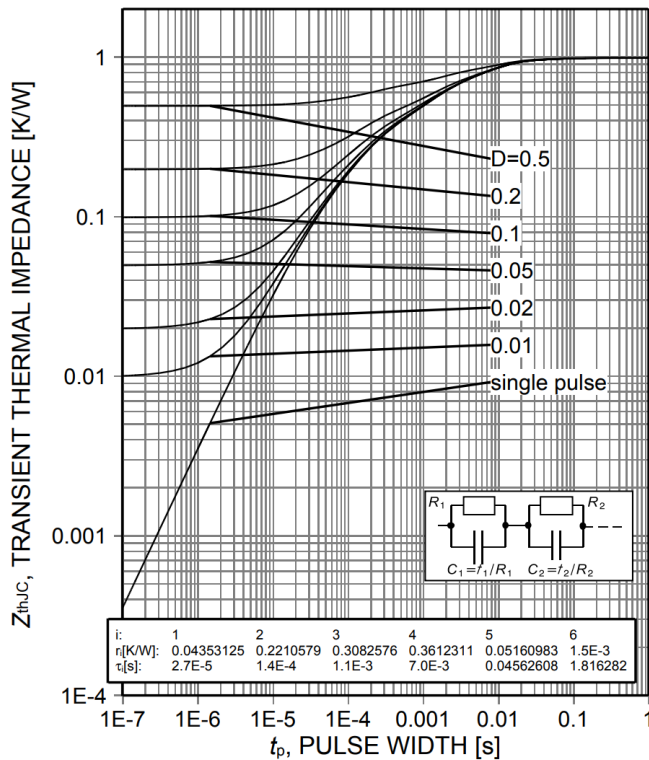


Figure 21. Typical diode transient thermal impedance as a function of pulse width ($D=t_p/T$)

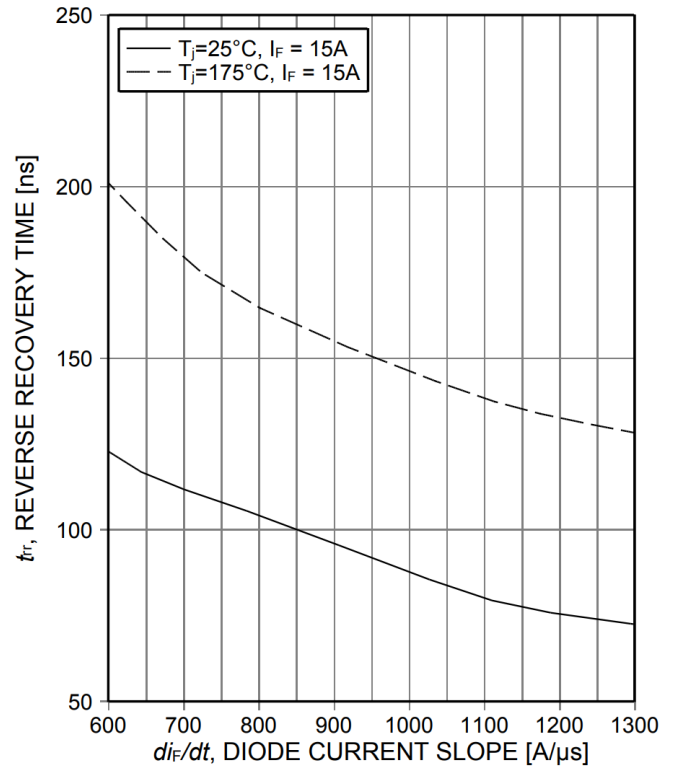


Figure 22. Typical reverse recovery time as a function of diode current slope ($V_R=400V$)

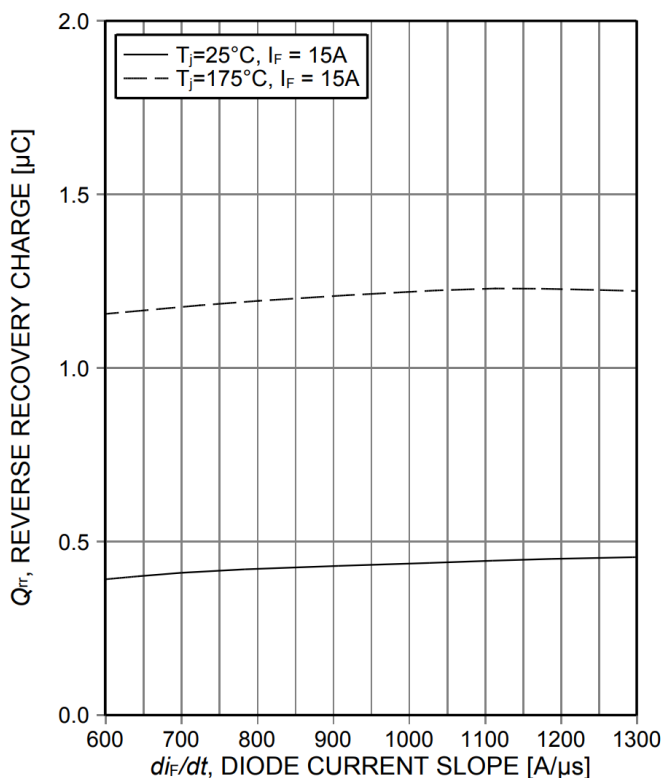


Figure 23. Typical reverse recovery charge as a function of diode current slope ($V_R=400V$)

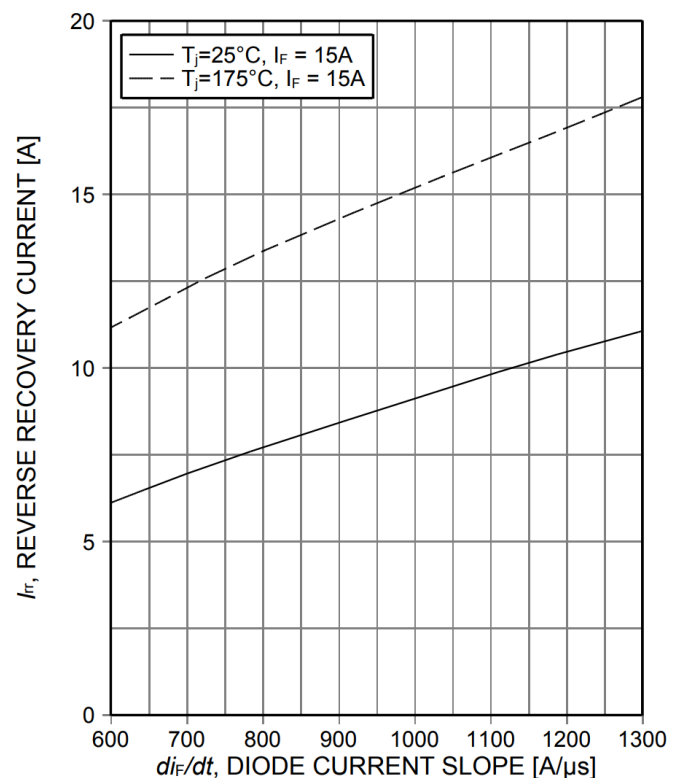


Figure 24. Typical reverse recovery current as a function of diode current slope ($V_R=400V$)

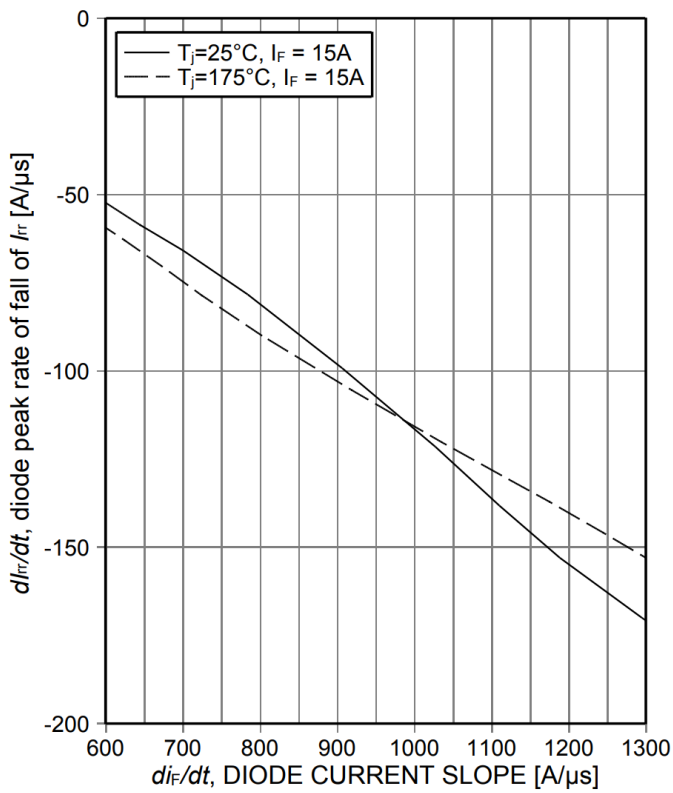


Figure 25. **Typical diode peak rate of fall of reverse recovery current as a function of diode current slope**
($V_R=400V$)

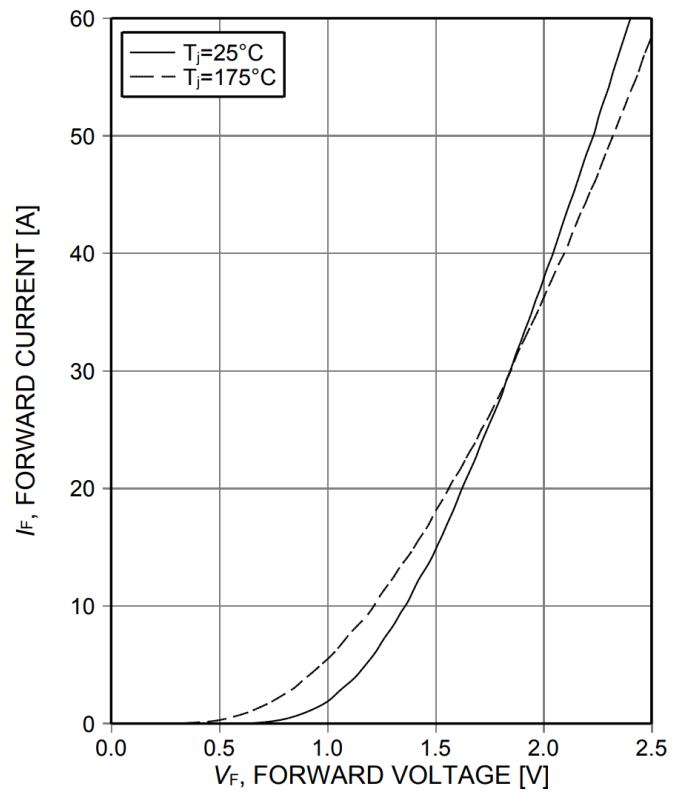


Figure 26. **Typical diode forward current as a function of forward voltage**

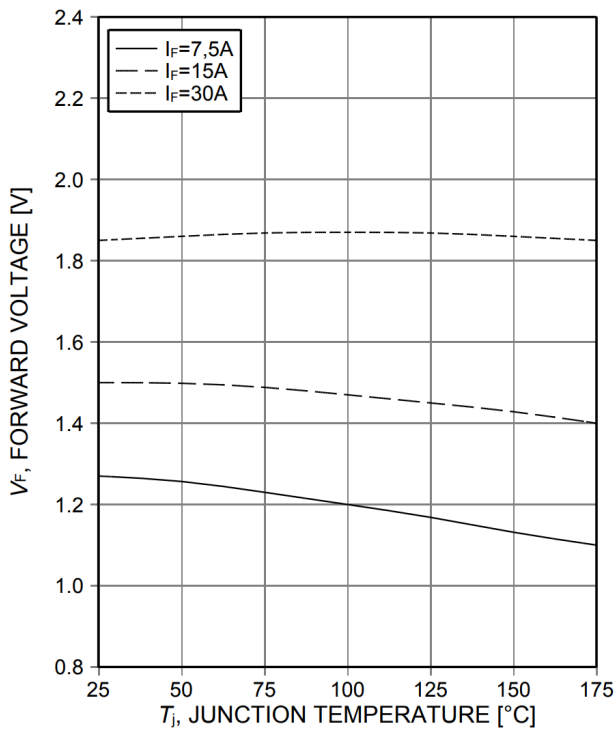
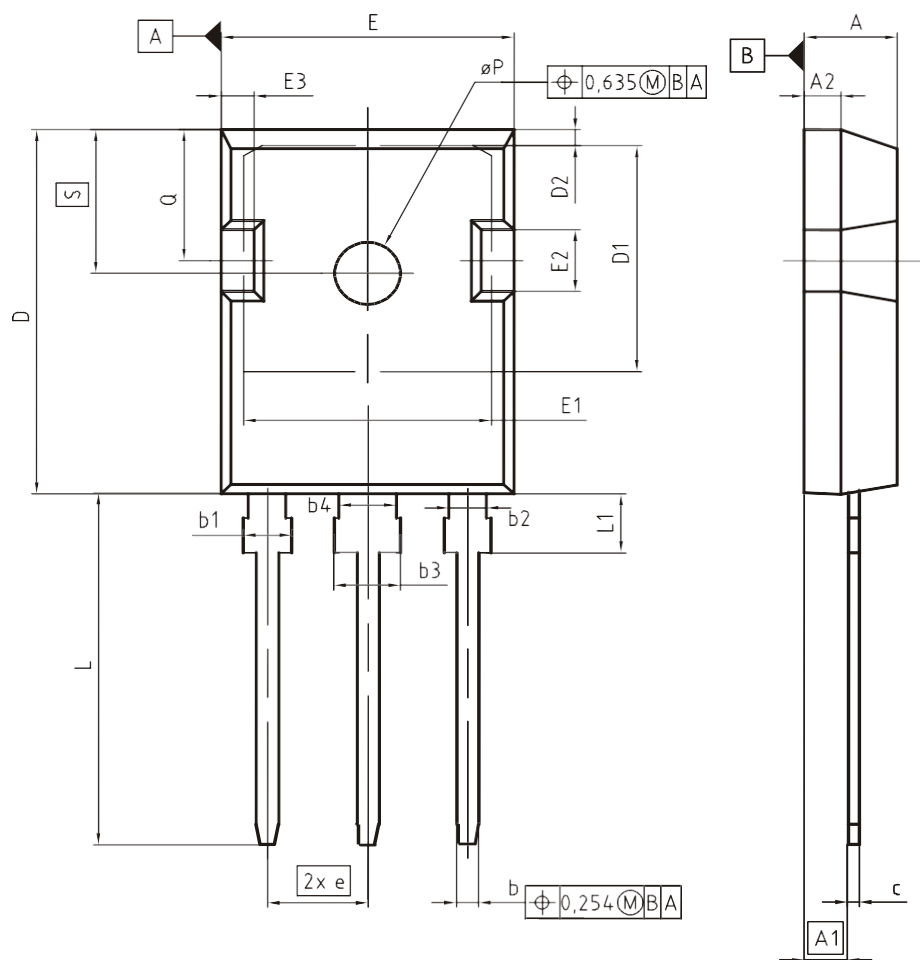
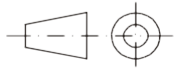


Figure 27. **Typical diode forward voltage as a function of junction temperature**

封装图 PG-T0247-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44 (BSC)		0.214 (BSC)	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
øP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

DOCUMENT NO. Z8B00003327
SCALE 0 5 5 7.5mm
EUROPEAN PROJECTION 
ISSUE DATE 09-07-2010
REVISION 05

测试条件

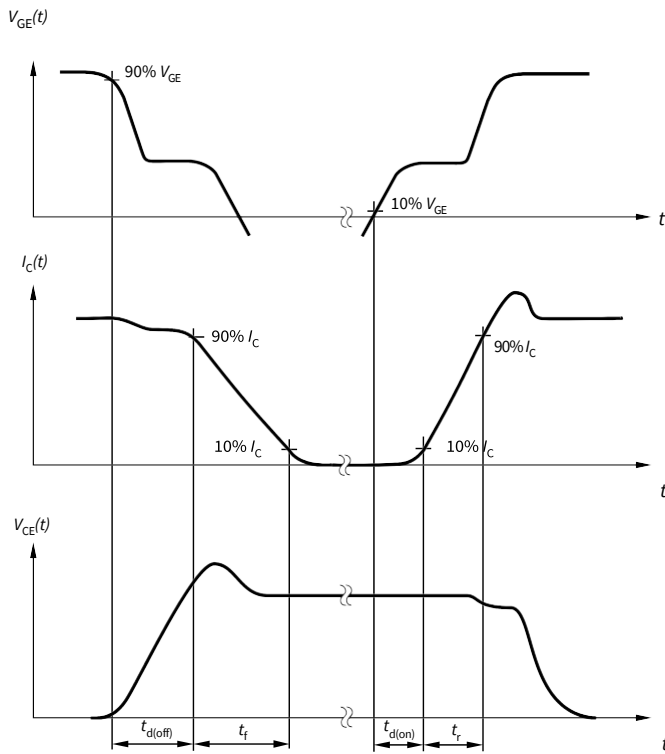


Figure A. Definition of switching times

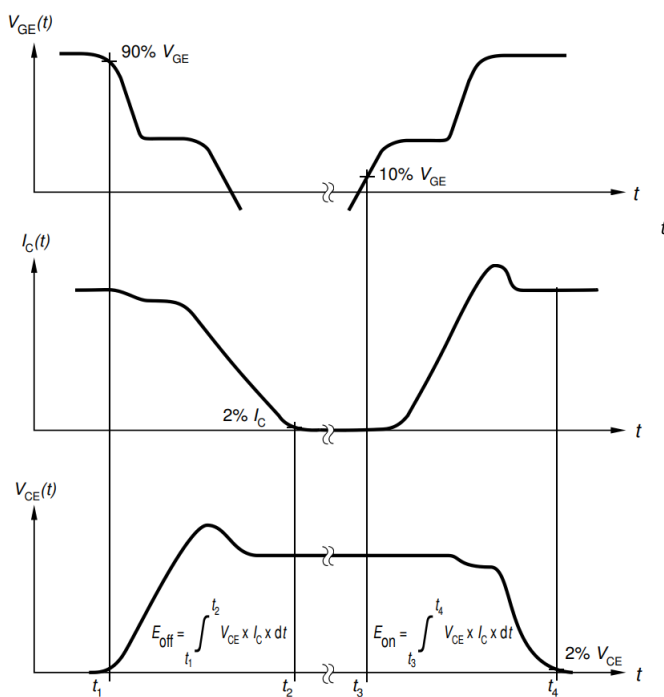


Figure B. Definition of switching losses

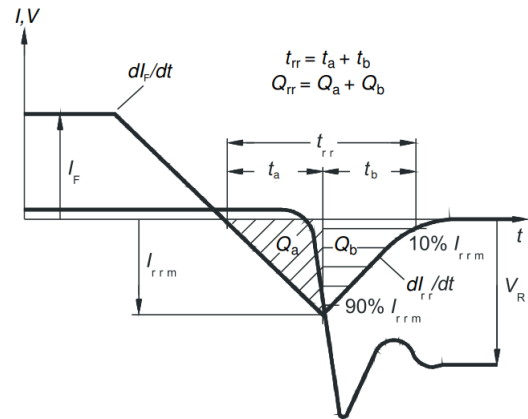


Figure C. Definition of diode switching characteristics

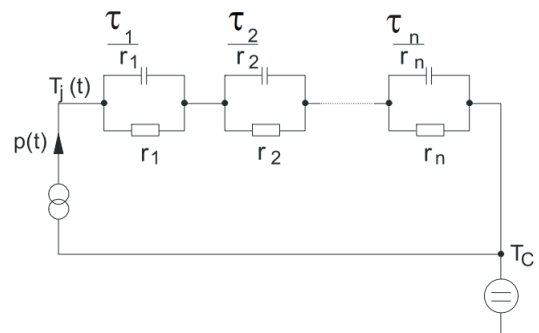


Figure D. Thermal equivalent circuit

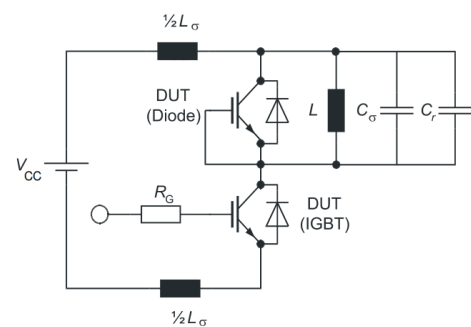


Figure E. Dynamic test circuit
Parasitic inductance L_σ ,
parasitic capacitor C_σ ,
relief capacitor C_r ,
(only for ZVT switching)

修订记录

IKW30N60DTP

Revision: 2016-02-08, Rev. 2.1

历史修订版本

Revision	Date	Subjects (major changes since last revision)
2.1	-	Release final datasheet

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